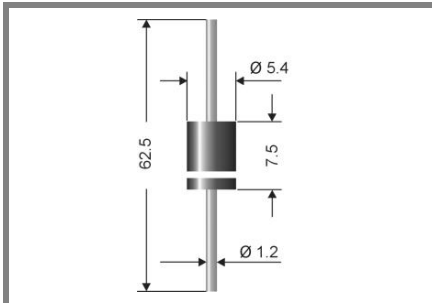


HE7A5



Axial lead diode

High efficiency silicon rectifier diode

HE7A5

Forward Current: 7,5 A

Reverse Voltage: 50 to 50 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case 5,4 x 7,5 [mm]
- Weight approx.: 1,4 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 1250 pieces per ammo

1) Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

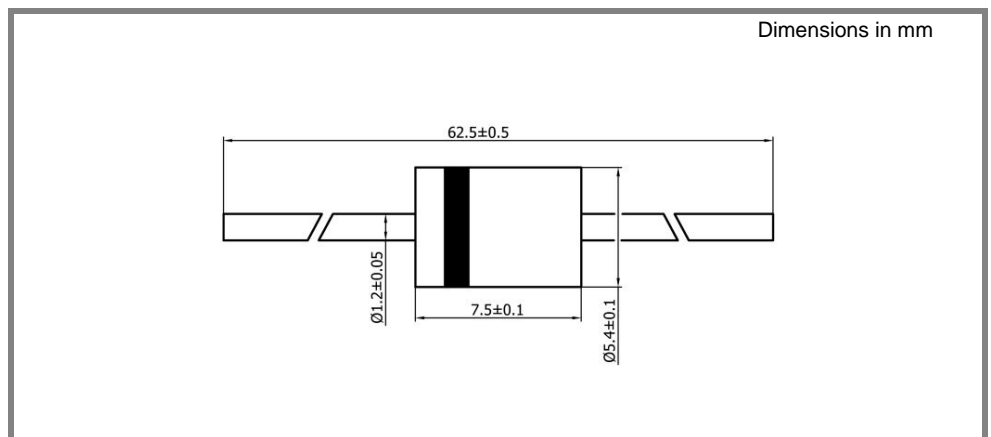
2) $I_F = 5 \text{ A}$, $T_j = 25 \text{ °C}$

3) $T_A = 25 \text{ °C}$

Type	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time	Max. forward voltage
HE7A5	V_{RRM} V 50	V_{RSM} V 80	$I_F = - \text{A}$ $I_R = - \text{A}$ $I_{RR} = - \text{A}$ t_{rr} ns -	$V_F^{(2)}$ 0,88

Absolute Maximum Ratings		$T_c = 25 \text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 75 \text{ °C}^{(1)}$	7,5	A
I_{FRM}	Repetitive peak forward current $f > 15 \text{ Hz}^{(1)}$	25	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave $^{(3)}$	300	A
i^2t	Rating for fusing, $t < 10 \text{ ms}^{(3)}$	450	A ² s
R_{thA}	Max. thermal resistance junction to ambient $^{(1)}$	60	K/W
R_{thT}	Max. thermal resistance junction to terminals $^{(1)}$	-	K/W
T_j	Operating junction temperature	-55...+150	°C
T_s	Storage temperature	-55...+150	°C

Characteristics		$T_c = 25 \text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25 \text{ °C}$; $V_R = V_{RRM}$	<10	μA
	$T_j = \text{°C}$; $V_R = V_{RRM}$		
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)	-	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = \text{mA}$; $T_j = \text{°C}$; inductive load switched off)	-	mJ



case: 5,4 x 7,5 [mm]

